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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

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Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8547vtatgd

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Overview

- AESU-Advanced Encryption Standard unit
 - Implements the Rijndael symmetric key cipher
 - ECB, CBC, CTR, and CCM modes
 - 128-, 192-, and 256-bit key lengths
- AFEU—ARC four execution unit
 - Implements a stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
- MDEU—message digest execution unit
 - SHA with 160- or 256-bit message digest
 - MD5 with 128-bit message digest
 - HMAC with either algorithm
- KEU—Kasumi execution unit
 - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
 - Also supports A5/3 and GEA-3 algorithms
- RNG—random number generator
- XOR engine for parity checking in RAID storage applications
- Dual I²C controllers
 - Two-wire interface
 - Multiple master support
 - Master or slave I^2C mode support
 - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
 - Optionally loads configuration data from serial ROM at reset via the I^2C interface
 - Can be used to initialize configuration registers and/or memory
 - Supports extended I²C addressing mode
 - Data integrity checked with preamble signature and CRC
- DUART
 - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data bus operating at up to 133 MHz
 - Eight chip selects support eight external slaves
 - Up to eight-beat burst transfers
 - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)

NOTE

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the device.

4.3 eTSEC Gigabit Reference Clock Timing

The following table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the device.

Parameter/Condition	Symbol	Min	Тур	Мах	Unit	Notes
EC_GTX_CLK125 frequency	f _{G125}	—	125	—	MHz	
EC_GTX_CLK125 cycle time	t _{G125}	—	8	—	ns	
EC_GTX_CLK125 rise and fall time L/TVDD = 2.5 V L/TVDD = 3.3 V	t _{G125R} , t _{G125F}	_	_	0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t _{G125H} /t _{G125}	45 47	_	55 53	%	2, 3

Table 6. EC_	GTX_CLK125	AC Timing	Specifications
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Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TV_{DD} = 2.5 V, and from 0.6 and 2.7 V for L/TV_{DD} = 3.3 V.

- 2. Timing is guaranteed by design and characterization.
- 3. EC_GTX_CLK125 is used to generate the GTX clock TSEC*n*_GTX_CLK for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the TSEC*n*_GTX_CLK. See Section 8.2.6, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 PCI/PCI-X Reference Clock Timing

When the PCI/PCI-X controller is configured for asynchronous operation, the reference clock for the PCI/PCI-x controller is not the SYSCLK input, but instead the PCIn_CLK. The following table provides the PCI/PCI-X reference clock AC timing specifications for the device.

	Table 7.	PCIn_	CLK AC	Timing	S	pecifications
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At recommended operating conditions (see Table 2) with $OV_{DD} = 3.3 \text{ V} \pm 165 \text{ mV}$.

Parameter/Condition	Symbol	Min	Тур	Max	Unit	Notes
PCIn_CLK frequency	f _{PCICLK}	16	_	133	MHz	—
PCIn_CLK cycle time	t _{PCICLK}	7.5	_	60	ns	—
PCIn_CLK rise and fall time	t _{PCIKH} , t _{PCIKL}	0.6	1.0	2.1	ns	1, 2
PCIn_CLK duty cycle	t _{PCIKHKL} /t _{PCICLK}	40		60	%	2

Notes:

1. Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.

2. Timing is guaranteed by design and characterization.

5 **RESET** Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Parameter/Condition	Min	Мах	Unit	Notes
Required assertion time of HRESET	100	—	μS	—
Minimum assertion time for SRESET	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before HRESET negation	100	—	μS	—
Input setup time for POR configs (other than PLL config) with respect to negation of HRESET	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of HRESET	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of HRESET	—	5	SYSCLKs	1

Table 8. RESE1	Initialization	Timing	Specifications
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Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Мах	Unit
Core and platform PLL lock times	—	100	μS
Local bus PLL lock time	—	50	μS
PCI/PCI-X bus PLL lock time	—	50	μS

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements.

Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10.	Power	Supply	Ramp	Rate
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Parameter	Min	Мах	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	_	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.

2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, "PLL Power Supply Filtering," the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface. The DDR controller supports both DDR1 and DDR2 memories. DDR1 is supported with the following AC timings at data rates of 333 MHz. DDR2 is supported with the following AC timings at data rates down to 333 MHz.

6.2.1 DDR SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 1.8 \text{ V}$.

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions

Parameter	Symbol	Min	Мах	Unit
AC input low voltage	V _{IL}	—	MV _{REF} – 0.25	V
AC input high voltage	V _{IH}	MV _{REF} + 0.25	—	V

Table 17 provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 2.5 \text{ V}$.

Table 17. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Мах	Unit
AC input low voltage	V _{IL}	—	MV _{REF} – 0.31	V
AC input high voltage	V _{IH}	MV _{REF} + 0.31	—	V

This table provides the input AC timing specifications for the DDR SDRAM interface.

Table 18. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Мах	Unit	Notes
Controller Skew for MDQS—MDQ/MECC 533 MHz 400 MHz 333 MHz	^t ciskew	-300 -365 -390	300 365 390	ps	1, 2

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This must be subtracted from the total timing budget.

 The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: t_{DISKEW} = ± (T/4 – abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.

DDR and DDR2 SDRAM

Table 19. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MDQS epilogue end	t _{DDKHME}	-0.6	0.6	ns	6

Notes:

- The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state)</sub> for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
- 2. All MCK/MCK referenced measurements are made from the crossing of the two signals ±0.1 V.
- 3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ/MECC/MDM/MDQS.
- 4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This is typically set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the MPC8548E PowerQUICC III Integrated Processor Reference Manual for a description and understanding of the timing modifications enabled by use of these bits.
- Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe must be centered inside of the data eye at the pins of the microprocessor.
- 6. All outputs are referenced to the rising edge of MCK[*n*] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

For the ADDR/CMD setup and hold specifications in Table 19, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.

Figure 3 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).



Figure 8 shows the GMII transmit AC timing diagram.



Figure 8. GMII Transmit AC Timing Diagram

8.2.2.2 GMII Receive AC Timing Specifications

This table provides the GMII receive AC timing specifications.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RX_CLK clock period	t _{GRX}	_	8.0	—	ns
RX_CLK duty cycle	t _{GRXH} /t _{GRX}	35	_	75	ns
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t _{GRDVKH}	2.0	_	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t _{GRDXKH}	0	_	—	ns
RX_CLK clock rise (20%-80%)	t _{GRXR} 2	—	_	1.0	ns
RX_CLK clock fall time (80%-20%)	t _{GRXF} 2	—		1.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

2. Guaranteed by design.

Figure 9 provides the AC test load for eTSEC.



Table 34. RMII Transmit A	C Timing	Specifications	(continued)
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Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
TSEC <i>n_</i> TX_CLK to RMII data TXD[1:0], TX_EN delay	t _{RMTDX}	1.0		10.0	ns

Note:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub></sub>

Figure 18 shows the RMII transmit AC timing diagram.



Figure 18. RMII Transmit AC Timing Diagram

8.2.7.2 RMII Receive AC Timing Specifications

Table 35. RMII Receive AC Timing Specifications

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
TSEC <i>n</i> _TX_CLK clock period	t _{RMR}	15.0	20.0	25.0	ns
TSEC <i>n</i> _TX_CLK duty cycle	t _{RMRH}	35	50	65	%
TSEC <i>n</i> _TX_CLK peak-to-peak jitter	t _{RMRJ}	—	_	250	ps
Rise time TSEC <i>n</i> _TX_CLK(20%–80%)	t _{RMRR}	1.0	_	2.0	ns
Fall time TSEC <i>n</i> _TX_CLK (80%–20%)	t _{RMRF}	1.0	_	2.0	ns
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK rising edge	t _{RMRDV}	4.0	_	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK rising edge	t _{RMRDX}	2.0	_	—	ns

Note:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}}

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t _{LBK}	7.5	12	ns	2
Local bus duty cycle	t _{LBKH/} t _{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	t _{LBKSKEW}	_	150	ps	7, 8
Input setup to local bus clock (except LGTA/UPWAIT)	t _{LBIVKH1}	1.9	—	ns	3, 4
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKH2}	1.8	—	ns	3, 4
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	1.1	—	ns	3, 4
LGTA/LUPWAIT input hold from local bus clock	t _{LBIXKH2}	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t _{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	t _{LBKHOV1}	_	2.1	ns	—
Local bus clock to data valid for LAD/LDP	t _{LBKHOV2}		2.3	ns	3
Local bus clock to address valid for LAD	t _{LBKHOV3}		2.4	ns	3
Local bus clock to LALE assertion	t _{LBKHOV4}		2.4	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	t _{LBKHOX1}	0.8	—	ns	3
Output hold from local bus clock for LAD/LDP	t _{LBKHOX2}	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	t _{LBKHOZ1}		2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ2}		2.6	ns	5

Table 41 describes the timing parameters of the local bus interface at $BV_{DD} = 2.5$ V.

Table 41. Local Bus Timing Parameters (BV_{DD} = 2.5 V)—PLL Enabled

Notes:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKH0X} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
</sub></sub>

- 2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
- 3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
- 4. Input timings are measured at the pin.

5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

- 6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
- Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV_{DD}/2.
- 8. Guaranteed by design.

Figure 22 provides the AC test load for the local bus.



Figure 22. Local Bus AC Test Load

NOTE

PLL bypass mode is required when LBIU frequency is at or below 83 MHz. When LBIU operates above 83 MHz, LBIU PLL is recommended to be enabled.

Figure 23 through Figure 28 show the local bus signals.



This table describes the timing parameters of the local bus interface at $BV_{DD} = 3.3$ V with PLL disabled.

Table 42. Local Bus Timing	Parameters—PLL Bypassed
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Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t _{LBK}	12	—	ns	2
Local bus duty cycle	t _{LBKH/} t _{LBK}	43	57	%	—
Internal launch/capture clock to LCLK delay	t _{lbkhkt}	2.3	4.4	ns	8
Input setup to local bus clock (except LGTA/LUPWAIT)	t _{LBIVKH1}	6.2	—	ns	4, 5
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKL2}	6.1	—	ns	4, 5
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	-1.8	—	ns	4, 5

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

12.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the JTAG interface.

Parameter	Symbol ¹	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current ($V_{IN}^{1} = 0 V \text{ or } V_{IN} = V_{DD}$)	I _{IN}	—	±5	μΑ
High-level output voltage ($OV_{DD} = min, I_{OH} = -2 mA$)	V _{OH}	2.4	—	V
Low-level output voltage (OV _{DD} = min, I _{OL} = 2 mA)	V _{OL}	—	0.4	V

 Table 43. JTAG DC Electrical Characteristics

Note:

1. Note that the symbol V_{IN} in this case, represents the OV_{IN}

12.2 JTAG AC Electrical Specifications

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 32.

Parameter	Symbol ²	Min	Мах	Unit	Notes
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} & t _{JTGF}	0	2	ns	6
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 0	_	ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	20 25		ns	4

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK)¹

Symbol	Parameter	Min	Nom	Max	Unit	Comments
T _{crosslink}	Crosslink random timeout	0		1	ms	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one downstream and one upstream port. See Note 7.

Notes:

1. No test load is necessarily associated with this value.

- 2. Specified at the measurement point into a timing and voltage compliance test load as shown in Figure 50 and measured over any 250 consecutive TX UIs. (Also see the transmitter compliance eye diagram shown in Figure 48.)
- 3. A T_{TX-EYE} = 0.70 UI provides for a total sum of deterministic and random jitter budget of T_{TX-JITTER-MAX} = 0.30 UI for the transmitter collected over any 250 consecutive TX UIs. The T_{TX-EYE-MEDIAN-to-MAX-JITTER} median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. Note that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
- 4. The transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D- line (that is, as measured by a vector network analyzer with 50- Ω probes—see Figure 50). Note that the series capacitors C_{TX} is optional for the return loss measurement.
- 5. Measured between 20%–80% at transmitter package pins into a test load as shown in Figure 50 for both V_{TX-D+} and V_{TX-D-}.
- 6. See Section 4.3.1.8 of the PCI Express Base Specifications Rev 1.0a.
- 7. See Section 4.2.6.3 of the PCI Express Base Specifications Rev 1.0a.
- 8. MPC8548E SerDes transmitter does not have CTX built in. An external AC coupling capacitor is required.

17.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 48 is specified using the passive compliance/test measurement load (see Figure 50) in place of any real PCI Express interconnect +RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit is always relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (for example, least squares and median deviation fits).

18.5 Explanatory Note on Transmitter and Receiver Specifications

AC electrical specifications are given for transmitter and receiver. Long- and short-run interfaces at three baud rates (a total of six cases) are described.

The parameters for the AC electrical specifications are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002.

XAUI has similar application goals to Serial RapidIO, as described in Section 8.1. The goal of this standard is that electrical designs for Serial RapidIO can reuse electrical designs for XAUI, suitably modified for applications at the baud intervals and reaches described herein.

18.6 Transmitter Specifications

LP-serial transmitter electrical and timing specifications are stated in the text and tables of this section.

The differential return loss, S11, of the transmitter in each case shall be better than:

- -10 dB for (baud frequency)/10 < Freq(f) < 625 MHz, and
- $-10 \text{ dB} + 10\log(f/625 \text{ MHz}) \text{ dB}$ for $625 \text{ MHz} \le \text{Freq}(f) \le \text{baud}$ frequency

The reference impedance for the differential return loss measurements is $100-\Omega$ resistive. Differential return loss includes contributions from on-chip circuitry, chip packaging, and any off-chip components related to the driver. The output impedance requirement applies to all valid output levels.

It is recommended that the 20%–80% rise/fall time of the transmitter, as measured at the transmitter output, in each case have a minimum value 60 ps.

It is recommended that the timing skew at the output of an LP-serial transmitter between the two signals that comprise a differential pair not exceed 25 ps at 1.25 GB, 20 ps at 2.50 GB, and 15 ps at 3.125 GB.

Characteristic Symbol Unit		Notos			
Characteristic	Symbol	Min	Max	Unit	NOIES
Output voltage	Vo	-0.40	2.30	V	Voltage relative to COMMON of either signal comprising a differential pair
Differential output voltage	V _{DIFFPP}	500	1000	mV p-p	_
Deterministic jitter	J _D	_	0.17	UI p-p	_
Total jitter	J _T	_	0.35	UI p-p	_
Multiple output skew	S _{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	800	800	ps	±100 ppm

Table 59. Short Run Transmitter AC Timing Specifications—1.25 GBaud

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_REQ[4:1]	AH2, AG4, AG3, AH4	I	OV _{DD}	—
				_
				_
				_
				_
PCI1_REQ0	AH3	I/O	OV _{DD}	—
PCI1_CLK	AH26	I	OV _{DD}	39
PCI1_DEVSEL	AH11	I/O	OV _{DD}	2
PCI1_FRAME	AE11	I/O	OV _{DD}	2
PCI1_IDSEL	AG9	I	OV _{DD}	—
PCI1_REQ64/PCI2_FRAME	AF14	I/O	OV _{DD}	2, 5, 10
PCI1_ACK64/PCI2_DEVSEL	V15	I/O	OV _{DD}	2
PCI2_CLK	AE28	I	OV _{DD}	39
PCI2_IRDY	AD26	I/O	OV _{DD}	2
PCI2_PERR	AD25	I/O	OV _{DD}	2
PCI2_GNT[4:1]	AE26, AG24, AF25, AE25	0	OV _{DD}	5, 9, 35
PCI2_GNT0	AG25	I/O	OV _{DD}	_
PCI2_SERR	AD24	I/O	OV _{DD}	2, 4
PCI2_STOP	AF24	I/O	OV _{DD}	2
PCI2_TRDY	AD27	I/O	OV _{DD}	2
PCI2_REQ[4:1]	AD28, AE27, W17, AF26	I	OV _{DD}	—
PCI2_REQ0	AH25	I/O	OV _{DD}	—
	DDR SDRAM Memory Interface			
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	0	GV _{DD}	
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	_
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	_
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	0	GV _{DD}	_
MBA[0:2]	F7, J7, M11	0	GV _{DD}	_

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV _{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV _{DD}	_
TV _{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV _{DD}	_
GV _{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV _{DD}	
BV _{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV _{DD}	_
V _{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V _{DD}	_
SV _{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV _{DD}	
XV _{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV _{DD}	_
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	_	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	_	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Powerfor CCB PLL (1.1 V)		26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)		26
SENSEVDD	M14	0	V _{DD}	13

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SENSEVSS	M16	—	—	13
	Analog Signals			
MVREF	A18	I Reference voltage signal for DDR	MVREF	
SD_IMP_CAL_RX	L28	I	200Ω to GND	_
SD_IMP_CAL_TX	AB26	I	100Ω to GND	
SD_PLL_TPA	U26	0	—	24

Table 71. MPC8548E Pinout Listing (continued)

Notes:

1. All multiplexed signals are listed only once and do not re-occur. For example, LCS5/DMA_REQ2 is listed only once in the local bus controller section, and is not mentioned in the DMA section even though the pin also functions as DMA_REQ2.

- 2. Recommend a weak pull-up resistor (2-10 kΩ) be placed on this pin to OV_{DD}.
- 3. A valid clock must be provided at POR if TSEC4_TXD[2] is set = 1.
- 4. This pin is an open drain signal.
- 5. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pullup or active driver is needed.
- 6. Treat these pins as no connects (NC) unless using debug address functionality.
- The value of LA[28:31] during reset sets the CCB clock to SYSCLK PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See Section 20.2, "CCB/SYSCLK PLL Ratio."
- 8. The value of LALE, LGPL2, and LBCTL at reset set the e500 core clock to CCB clock PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See the Section 20.3, "e500 Core PLL Ratio."
- 9. Functionally, this pin is an output, but structurally it is an I/O because it either samples configuration input during reset or because it has other manufacturing test functions. This pin therefore is described as an I/O for boundary scan.
- 10. This pin functionally requires a pull-up resistor, but during reset it is a configuration input that controls 32- vs. 64-bit PCI operation. Therefore, it must be actively driven low during reset by reset logic if the device is to be configured to be a 64-bit PCI device. See the *PCI Specification*.
- 11. This output is actively driven during reset rather than being three-stated during reset.
- 12. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
- 13. These pins are connected to the V_{DD}/GND planes internally and may be used by the core power supply to improve tracking and regulation.
- 14.Internal thermally sensitive resistor.
- 15.No connections must be made to these pins if they are not used.
- 16. These pins are not connected for any use.
- 17.PCI specifications recommend that a weak pull-up resistor (2–10 kΩ) be placed on the higher order pins to OV_{DD} when using 64-bit buffer mode (pins PCI_AD[63:32] and PCI1_C_BE[7:4]).
- 19.If this pin is connected to a device that pulls down during reset, an external pull-up is required to drive this pin to a safe state during reset.
- 20. This pin is only an output in FIFO mode when used as Rx flow control.

24.Do not connect.

Table 72	. MPC8547E	Pinout Listing	(continued)
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Signal	Package Pin Number	Pin Type	Power Supply	Notes
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV _{DD}	_
IRQ[8]	AF19	I	OV _{DD}	—
IRQ[9]/DMA_DREQ3	AF21	I	OV _{DD}	1
IRQ[10]/DMA_DACK3	AE19	I/O	OV _{DD}	1
IRQ[11]/DMA_DDONE3	AD20	I/O	OV _{DD}	1
IRQ_OUT	AD18	0	OV _{DD}	2, 4
	Ethernet Management Interface			•
EC_MDC	AB9	0	OV _{DD}	5, 9
EC_MDIO	AC8	I/O	OV _{DD}	—
	Gigabit Reference Clock		•	
EC_GTX_CLK125	V11	I	LV _{DD}	—
Th	ree-Speed Ethernet Controller (Gigabit Ethern	et 1)		
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV _{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	0	LV _{DD}	5, 9
TSEC1_COL	R4	I	LV _{DD}	—
TSEC1_CRS	V5	I/O	LV _{DD}	20
TSEC1_GTX_CLK	U7	0	LV _{DD}	—
TSEC1_RX_CLK	U3	I	LV _{DD}	—
TSEC1_RX_DV	V2	I	LV _{DD}	—
TSEC1_RX_ER	T1	I	LV _{DD}	—
TSEC1_TX_CLK	Т6	I	LV _{DD}	—
TSEC1_TX_EN	U9	0	LV _{DD}	30
TSEC1_TX_ER	Τ7	0	LV _{DD}	—
Th	ree-Speed Ethernet Controller (Gigabit Ethern	et 2)		
TSEC2_RXD[7:0]	P2, R2, N1, N2, P3, M2, M1, N3	I	LV _{DD}	—
TSEC2_TXD[7:0]	N9, N10, P8, N7, R9, N5, R8, N6	0	LV _{DD}	5, 9, 33
TSEC2_COL	P1	I	LV _{DD}	—
TSEC2_CRS	R6	I/O	LV _{DD}	20
TSEC2_GTX_CLK	P6	0	LV _{DD}	—
TSEC2_RX_CLK	N4	I	LV _{DD}	—
TSEC2_RX_DV	P5	I	LV _{DD}	—
TSEC2_RX_ER	R1	I	LV _{DD}	—
TSEC2_TX_CLK	P10	I	LV _{DD}	—
TSEC2_TX_EN	P7	0	LV _{DD}	30

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_TRDY	AG11	I/O	OV _{DD}	2
PCI1_REQ[4:1]	AH2, AG4, AG3, AH4	ļ	OV _{DD}	—
PCI1_REQ0	AH3	I/O	OV _{DD}	—
PCI1_CLK	AH26	I	OV _{DD}	39
PCI1_DEVSEL	AH11	I/O	OV _{DD}	2
PCI1_FRAME	AE11	I/O	OV _{DD}	2
PCI1_IDSEL	AG9	I	OV _{DD}	—
cfg_pci1_width	AF14	I/O	OV _{DD}	112
Reserved	V15	_	_	110
Reserved	AE28	_	_	2
Reserved	AD26	_	_	110
Reserved	AD25	_	_	110
Reserved	AE26	_	_	110
cfg_pci1_clk	AG24	I	OV _{DD}	5
Reserved	AF25	_	_	101
Reserved	AE25	_	_	110
Reserved	AG25	_	_	110
Reserved	AD24	_	_	110
Reserved	AF24	_	_	110
Reserved	AD27	_	_	110
Reserved	AD28, AE27, W17, AF26	_	_	110
Reserved	AH25	_	_	110
	DDR SDRAM Memory Interface			
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	_
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	0	GV _{DD}	
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	_
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	0	GV _{DD}	—
MBA[0:2]	F7, J7, M11	0	GV _{DD}	_

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TV _{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV _{DD}	_
GV _{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V,2.5 V)	GV _{DD}	_
BV _{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV _{DD}	—
V _{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V _{DD}	_
SV _{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV _{DD}	_
XV _{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV _{DD}	_
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	_	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	_	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	Ι	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	_	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	_	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	0	V _{DD}	13

Table 74. MPC8543E Pinout Listing (continued)

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	R_{\thetaJB}	3	°C/W	3
Die junction-to-case	N/A	$R_{ extsf{ heta}JC}$	0.8	°C/W	4

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Notes:

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
- 3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package	Thermal	Characteristics	for FC-PBGA
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Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	9	°C/W	1, 2